

IN THE SPECIFICATION

Please replace the paragraph at page 15, lines 5-18, with the following rewritten paragraph:

In a structure shown in FIG. 1, if a fabrication process of forming ~~another~~ other n-type diffusion layers under the field oxide is available, a structure of connecting the photodetector layer to the floating diffusion layers, which serve as the sources (or drains) of the MOS transistors via the n-type diffusion layers (13 and 14) is possible, as shown in FIG. 7. When a wide (along the depth direction to the plane of the paper) gate width of a photodetector layer is designed so as to ensure a sufficiently large optical detection area, the greater the area of the high-concentration source or drain region of the MOS transistor, the more the dark current increases and the more the capacitance also increases, decreasing the voltage sensitivity. Therefore, as shown in FIG. 7, the n-type diffusion layers are provided so that the n-type diffusion layers can capture electrons generated in the photodetector layer.

Please cancel the original Abstract at page 24, lines 1-17 in its entirety and insert therefor the following replacement Abstract on a separate sheet as follows: